

Docket No. YOR920000644US1
Application No. 10/042,181



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MAR 21 2003
TECHNOLOGY
10/A 3-25-03
A. Webb

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Bojarczuk et al.

Serial No.: 10/042,181

Group Art Unit: 2824

Filed: January 11, 2002

Examiner: Bradley Smith

For: RARE EARTH METAL OXIDE MEMORY ELEMENT BASED ON CHARGE
STORAGE AND METHOD FOR MANUFACTURING SAME (as amended)

Assistant Commissioner of Patents
Washington, D.C. 20231

AMENDMENT UNDER 37. C.F.R. §1.111

Sir:

In response to the Office Action dated November 15, 2002, please amend the
above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 15-23 without prejudice or disclaimer.

1. (Amended) A data storage element, comprising:

a substrate comprising a semiconductor material;

A
a metal oxide layer comprising an electrically insulating rare earth metal oxide disposed
upon a surface of said substrate;

a conductive material disposed upon said metal oxide layer;

a first electrode electrically connected to said conductive material; and